

Appl. No. 10/697,139
Reply to Office action of 01/31/2005

Amendments to the Specification:

Please amend paragraph [0024] as shown below:

[0024] Referring to FIG. 2D, the protective overcoat 116 is deposited. In the preferred embodiment, an etchstop layer 114 of, for example, SiN or SiC is first deposited over the surface followed by the deposition of the protective overcoat 116. For example, protective overcoat 116 may comprise a silicon-oxynitride or oxide layer. Protective overcoat 116, etchstop layer 114, and protect layer 109 are then patterned and etched to expose a portion of metal interconnect line 104b and a portion of top electrode 112-114 as well as all other areas of the device where external connections are desired (i.e., bondpad areas).

Please amend paragraph [0025] as shown below:

[0025] Still referring to Fig. 2D, a metal capping layer 118 is deposited over the structure. Typically, metal capping layer 118 comprises aluminum to improve adhesion of the bond wires typically applied during packaging. Metal capping layer 118 is patterned and etched to provide individual caps (i.e., unconnected) for each bondpad, as is known in the art. However, where decoupling capacitors are placed, metal capping layer 118 connects between the top electrode 112 and a neighboring metal interconnect line 104b. FIG. 2E, shows a third metal interconnect line 104c having a standard metal cap 134-138.